

Silicon PNP Power Transistor

DESCRIPTION

- Collector Current $-I_C = -20A$
- Collector-Emitter Breakdown Voltage-
 $V_{(BR)CEO} = -45V(\text{Min})$ - BD746; $-60V(\text{Min})$ - BD746A
 $-80V(\text{Min})$ - BD746B; $-100V(\text{Min})$ - BD746C
- Complement to Type BD745/A/B/C

APPLICATIONS

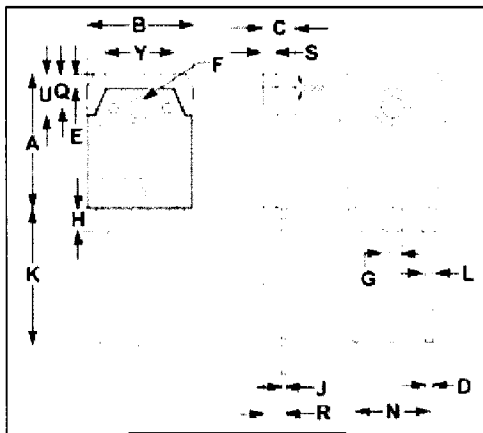
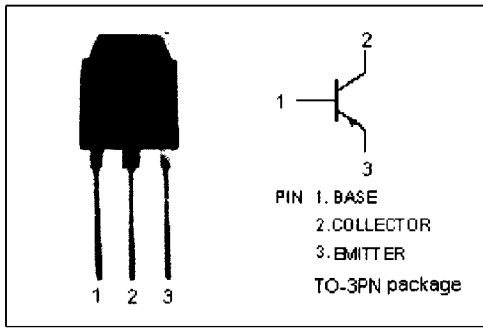
- Designed for use in general purpose power amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT	
V_{CER}	Collector-Emitter Voltage ($R_{BE} = 100 \Omega$)	BD746	-50	V
		BD746A	-70	
		BD746B	-90	
		BD746C	-110	
V_{CEO}	Collector-Emitter Voltage	BD746	-45	V
		BD746A	-60	
		BD746B	-80	
		BD746C	-100	
V_{EBO}	Emitter-Base Voltage	-5	V	
I_C	Collector Current-Continuous	-20	A	
I_{CM}	Collector Current-Peak	-25	A	
I_B	Base Current	-7	A	
P_C	Collector Power Dissipation @ $T_a=25^\circ C$	3.5	W	
	Collector Power Dissipation @ $T_c=25^\circ C$	115		
T_J	Junction Temperature	150	$^\circ C$	
T_{stg}	Storage Temperature Range	-65~150	$^\circ C$	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	1.1	$^\circ C/W$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.10
H	3.20	3.40
J	0.595	0.605
K	20.50	20.70
L	1.90	2.10
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.005
U	5.90	6.10
Y	9.90	10.10



Silicon PNP Power Transistor

BD746/A/B/C

ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	BD746	-45			V	
		BD746A	-60				
		BD746B ₂	-80				
		BD746C	-100				
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = -5A; I _B = -0.5A			-1.0	V	
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = -20A; I _B = -5A			-3.0	V	
V _{BE(on)-1}	Base-Emitter On Voltage	I _C = -5A; V _{CE} = -4V			-1.0	V	
V _{BE(on)-2}	Base-Emitter On Voltage	I _C = -20A; V _{CE} = -4V			-3.0	V	
I _{CES}	Collector Cutoff Current	BD746	V _{CE} = -50V; V _{BE} = 0 V _{CE} = -50V; V _{BE} = 0; T _C = 125°C			-0.1 -5.0	mA
		BD746A	V _{CE} = -70V; V _{BE} = 0 V _{CE} = -70V; V _{BE} = 0; T _C = 125°C			-0.1 -5.0	
		BD746B	V _{CE} = -90V; V _{BE} = 0 V _{CE} = -90V; V _{BE} = 0; T _C = 125°C			-0.1 -5.0	
		BD746C	V _{CE} = -110V; V _{BE} = 0 V _{CE} = -110V; V _{BE} = 0; T _C = 125°C			-0.1 -5.0	
I _{CEO}	Collector Cutoff Current	BD746/A	V _{CE} = -30V; I _B = 0			-0.1	mA
		BD746B/C	V _{CE} = -60V; I _B = 0				
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-0.5	mA	
h _{FE-1}	DC Current Gain	I _C = -1A; V _{CE} = -4V	40				
h _{FE-2}	DC Current Gain	I _C = -5A; V _{CE} = -4V	20		150		
h _{FE-3}	DC Current Gain	I _C = -20A; V _{CE} = -4V	5				

Switching times

t _d	Delay Time	I _C = -5A; I _{B1} = -I _{B2} = -0.5A; R _L = 6 Ω; V _{BE(off)} = 4.2V		0.02		μs
t _r	Rise Time			0.12		μs
t _s	Storage Time			0.60		μs
t _f	Fall Time			0.30		μs